



**Product data sheet** 

### 1. General description

Dual ultrafast power diodes in a TO3PF plastic package.

### 2. Features and benefits

- Very low on-state loss
- Reduces switching losses in associated MOSFET or IGBT
- Low leakage current
- Isolated plastic package

### 3. Applications

- Active PFC in air conditioner
- S.M.P.S Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies

### 4. Quick reference data

Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating	·					_
V <sub>R</sub>	repetitive peak reverse voltage	DC		600			V
I <sub>F(AV)</sub>	average forward current	δ = 0.5; T <sub>h</sub> ≤ 96 °C; square-wave pulse; per diode; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	15		A		
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5; $t_{p}$ = 25 µs; $T_{h} \leq$ 96 °C; square-wave pulse; per diode	30		A		
I <sub>FSM</sub>	non-repetitive peak forward current	t <sub>p</sub> = 10 ms; T <sub>j(lnit)</sub> = 25 °C; sine-wave pulse; per diode; <u>Fig. 4</u>	150		A		
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	165		A		
Symbol	Parameter	Conditions	N	lin	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	$I_F = 15 \text{ A}; T_j = 25 \text{ °C}; \text{ per diode}; Fig. 6$	-		1.8	2.1	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 150 °C; per diode; <u>Fig. 6</u>	-		1.3	1.6	V
Dynamic	characteristics		I		1		
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode } Fig. 7$	-		25	50	ns
		$I_F = 15 \text{ A}; V_R = 400 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode } \underline{\text{Fig. } 7}$	-		69	-	ns
		$I_F = 15 \text{ A}; V_R = 400 \text{ V}; \text{ d}_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_i = 125 \text{ °C}; \text{ per diode Fig. 7}$	-		100	-	ns

# **5. Pinning information**

Table 2.	. Pinning infor	mation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		
2	К	cathode	© © ©	
3	A2	anode 2		K 21/25
mb	n.c.	mounting base; isolated		sym125

## 6. Ordering information

Table 3. Ordering information								
Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date		
BYV415J-600P	TO3PF	BYV415J-600PQ	Tube	30	SOT1293	16-Mar-2006		

# 7. Marking

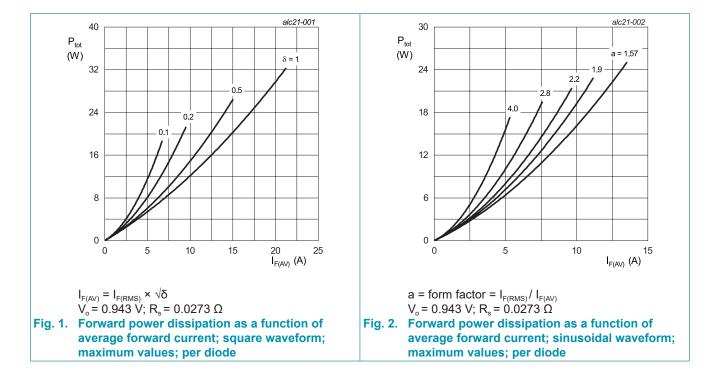
Table 4. Marking codes						
Type number	Marking codes					
BYV415J-600P	BYV415J-600P					

### 8. Limiting values

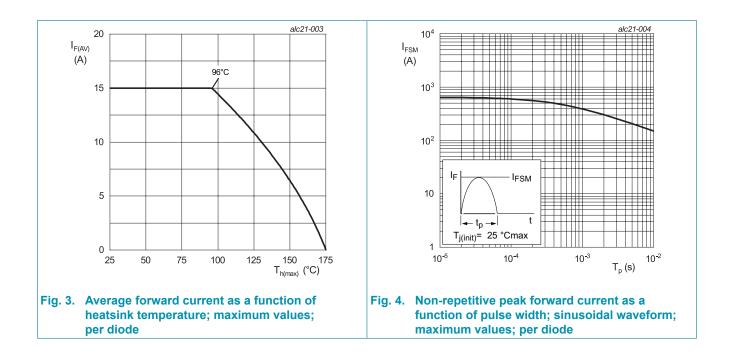
#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{\text{RRM}}$	repetitive peak reverse voltage		600	V
$V_{\text{RWM}}$	crest working reverse voltage		600	V
V <sub>R</sub>	reverse voltage	DC	600	V
$I_{F(AV)}$	average forward current	δ = 0.5; T <sub>h</sub> ≤ 96 °C; square-wave pulse; per diode; Fig. 1; Fig. 2; Fig. 3	15	A
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5; $t_p$ = 25 µs; $T_h \leq$ 96 °C; square-wave pulse; per diode	30	A
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	150	A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	165	A
T <sub>stg</sub>	storage temperature		-65 to 175	°C
Tj	junction temperature		175	°C

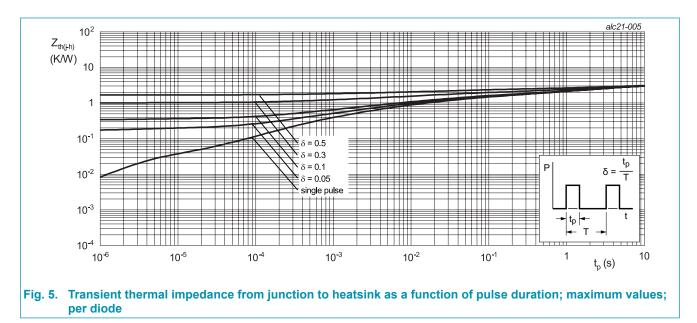


BYV415J-600P Dual ultrafast power diode



### 9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-h)</sub>	thermal resistance from junction to heatsink	with heatsink compound; per diode; Fig. <u>5</u>	-	-	3	K/W
		with heatsink compound; both diodes conducting	-	-	2.5	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	35	-	K/W



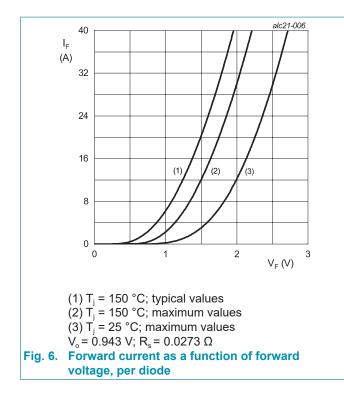
### 10. Isolation characteristics

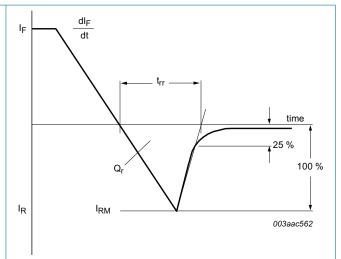
#### Table 7. Isolation characteristics **Symbol Parameter** Conditions Min Тур Max Unit 50 Hz $\leq$ f $\leq$ 60 Hz; RH $\leq$ 65 %; from all V RMS isolation voltage -2500 V<sub>isol(RMS)</sub> \_ pins to external heatsink; sinusoidal waveform: clean and dust free from cathode to external heatsink 10 $C_{isol}$ isolation capacitance -pF

**Dual ultrafast power diode** 

## **11. Characteristics**

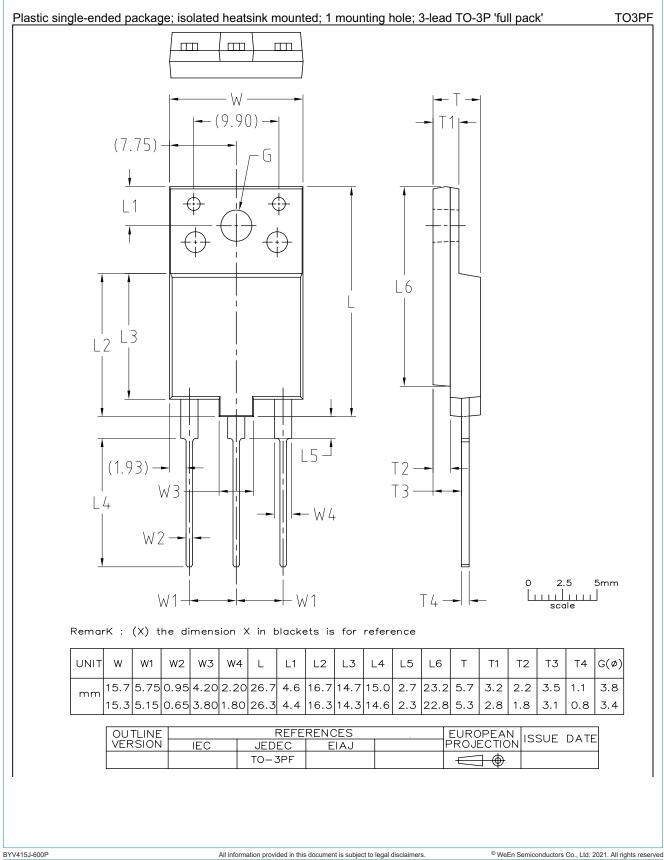
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		Conditions	INITI	Ч	WIAA	Unit
Static cha	aracteristics					
V <sub>F</sub>	forward voltage	$I_{F} = 15 \text{ A}; T_{j} = 25 \text{ °C}; \text{ per diode}; Fig. 6$	-	1.8	2.1	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 150 °C; per diode; <u>Fig. 6</u>	-	1.3	1.6	V
I <sub>R</sub>	reverse current	$V_R$ = 600 V; per diode; $T_j$ = 25 °C	-	-	10	μA
		$V_R$ = 600 V; per diode; $T_j$ = 150 °C	-	-	500	μA
Dynamic	characteristics					
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7$	-	25	50	ns
		$I_{F} = 15 \text{ A}; V_{R} = 400 \text{ V};  \text{d}_{\text{F}}/\text{d}\text{t} = 200 \text{ A}/\mu\text{s}; \\ T_{j} = 25 ^{\circ}\text{C}; \text{ per diode};  \text{Fig. 7}$	-	69	-	ns
		$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; \text{ per diode; } Fig. 7$	-	100	-	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7$	-	3.5	-	A
		$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; \text{ per diode}; \frac{\text{Fig. 7}}{2}$	-	7.6	-	A
Qr	recovered charge	$ \begin{array}{l} {\sf I}_{\sf F} = 15 \; {\sf A}; \; {\sf V}_{\sf R} = 400 \; {\sf V}; \; {\sf d}{\sf I}_{\sf F}/{\rm d}t = 200 \; {\sf A}/\mu {\sf s}; \\ {\sf T}_{\sf j} = 25 \; {\rm ^{\circ}C}; \; {\sf per} \; {\rm diode}; \; {\color{black} {\sf Fig. 7} \\ \end{array}                                 $	-	120	-	nC
		I <sub>F</sub> = 15 A; V <sub>R</sub> = 400 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>i</sub> = 125 °C; per diode; <u>Fig. 7</u>	-	380	-	nC





### Fig. 7. Reverse recovery definitions; ramp recovery

### 12. Package outline



### BYV415J-600P

#### Dual ultrafast power diode

# 13. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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